Types and structures:
- InGaAsP/InGaAsP-MQW and InGaAlAs/InGaAlAs-MQW
- RW, BH, and BA laser structures
- FP, DFB, DBR, multisection, EMLs, gain elements, monolithically integrated
- Flip-chip mountable (surface-n-contact)
- Integrated heater for wavelength tuning
- Electron beam defined DFB gratings
- Integrated beam forming (taper)

Laser Diodes and LEDs
- Wavelength range 1.2 - 1.9 µm
- Output power up to 700mW cw (BH, RW)
- Output power up to 18W pulse (BA)
- Modulation up to 25GHz (RW)
- Modulation up to 70GHz (EML)
- Uncooled operation

Our Services:
- Consulting and feasibility studies
- Development of components according to customer specifications, from simulation to prototypes ("tailored" wavelengths)
- Full or partial processing of laser diodes
- Low to medium volume production on own InP semiconductor processing line
- Cooperation with industrial partners for volume production

For more detailed information, references and offers please contact us

CONTACT
Dr. Martin Moehrle
Head of Laser Group
Photonic Components
Fraunhofer Heinrich Hertz Institute
Einsteinufer 37 10587 Berlin | Germany
phone +49 30 31002-724
e-mail: martin.moehrle@hhi.fraunhofer.de
www.hhi.fraunhofer.de

www.hhi.fraunhofer.de